Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supporting Information (SI)

Tailoring the structural and electronic properties of $SnSe_2/MoS_2$ van der Waals heterostructure by electric field and the insertion of graphene sheet

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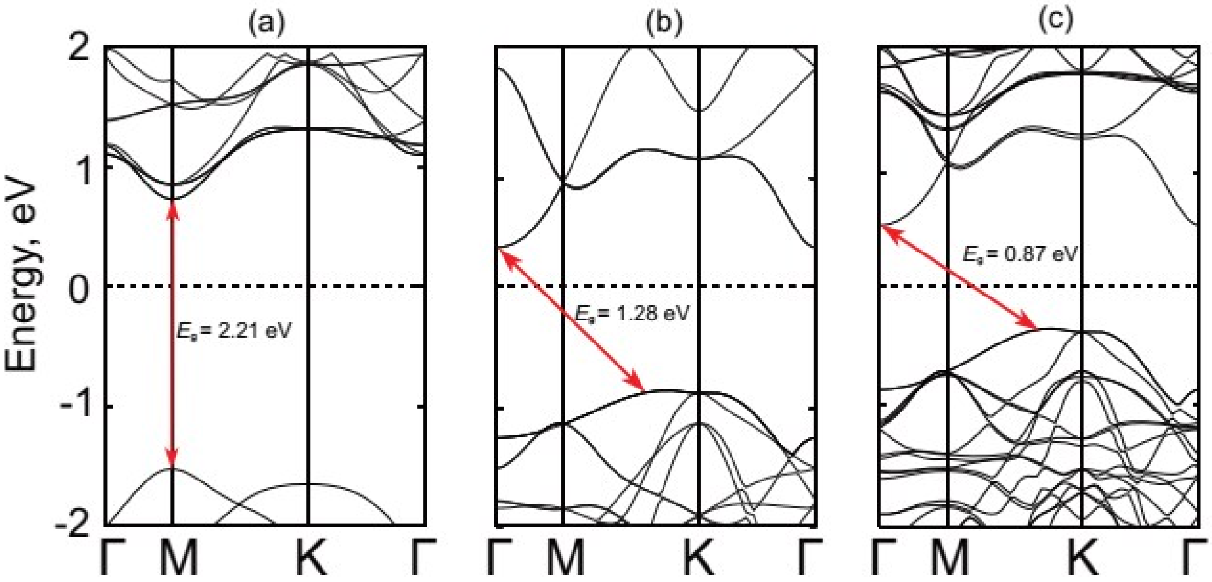

Fig. S1. Band structures of (a) MoS_2, (b) $SnSe_2$, and (c) $SnSe_2/MoS_2$ vdWH given by HSE06 method.

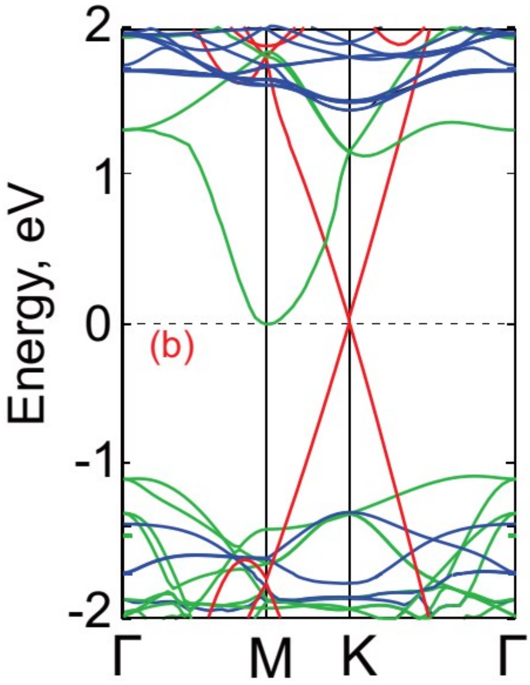

Fig. S2. Projected band structure of the $SnSe_2/G/MoS_2$ vdWH given by HSE06 method.

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